## **ELECTRONIC INFORMATION DISCLOSURE STATEMENT**

Electronic Version v18

Stylesheet Version v18.0

Title of Invention

STRUCTURE AND METHOD FOR SILICIDED METAL GATE TRANSISTORS

Application Number:

10/605,130

Confirmation Number:

First Named Applicant:

Bruce Doris

Attorney Docket Number:

FIS920030283US1

Art Unit:

Examiner:

Search string:

( 6033963 or 6492694 or 6528362 or 6534352 or 6544827 or 6589866 or

20030122202 ).pn

## **US Patent Documents**

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
BU	1	6033963	2000-03-07	Huang, et al.	7		
1	2	6492694	2002-12-10	Nobel, et al.			
	3	6528362	2003-03-04	Besser, et al.			
	4	6534352	2003-03-18	Kim			
	5	6544827	2003-04-08	Abiko			
B	6	6589866	2003-07-08	Besser, et al.	/		

## **US Published Applications**

Note: Applicant is not required to submit a paper copy of cited US Published Applications

init Cite.No	Pub. No.	Date	Applicant	Kind	Class	Subclass
DA 1	20030122202	2003-07-03	Kwon			

Signature

Examiner Name Date

PAGE 1 OF 1  FORM PTO-1449 (Modified)  SEP 2 9 2003  LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE SYSTEMENT							<del></del>	ATTY. DOCKET NO.		SERIAL NO.				
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1	Al	K. T	Symposium," <u>Mater. Res. Soc. Proc.</u> , vol. 716, 2002, pp. 85-90.  K. T. Nishinohara et al., "Regular Papers Short Notes & Review Papers" <u>Japan Jnl. App. Phys. Ltrs</u> , pt 1, v. 40, 2001, pp. 2603-2606.											
	AJ	F. F	F. F. Zhao et al., "Silicon Materials – Processing, Characterization and Reliability Symposium,"  Mater. Res. Soc. Proc., vol. 716, 2002, pp. 41-46.											
DN	AK	W.	T. Lia	aw et	al.,	"Letters" Japa	n Jnl.	App. Phys. Ltrs, pt 2, v. 3	6, n. 2A	1997, pp. L8	9-92.			
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